Product data sheet

1. General description

Dual ultrafast power diode in a SOT404 (D2PAK) surface-mountable plastic package.

2. Features and benefits

- · High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- · Soft recovery characteristic minimizes power consuming oscillations
- Surface-mountable package

3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit	
Absolute	maximum rating							
V_{RRM}	repetitive peak reverse voltage			2	200		V	
I _{O(AV)}	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 115$ °C; both diodes conducting; Fig. 1; Fig. 2	20		А			
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s;	0.2		А			
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	8		kV			
Static ch	aracteristics							
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	0.72	0.85	V	
		I _F = 20 A; T _j = 25 °C		-	1	1.15	V	
Dynamic	characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5		-	20	25	ns	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	F	
2	K	cathode [1]		A4 N . 14 A2
3	A2	anode 2		A1 A2
mb	K	mounting base; cathode	1 TO-263 (D2PAK)	K sym125

^[1] it is not possible to make a connection to pin 2 of the SOT404 package

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYV32EB-200	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV32EB-200	BYV32EB-200

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		200	V
V_{RWM}	crest working reverse voltage		200	V
V_R	reverse voltage	DC	200	V
I _{O(AV)}	average output current	δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; Fig 1; Fig 2	20	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \ \mu s$; $T_{mb} \le 115 \ ^{\circ}C$; per diode	20	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125	А
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137	А
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s; per diode	0.2	А
I _{RSM}	non-repetitive peak reverse current	t_p = 100 μ s; per diode	0.2	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C
V _{ESD}	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 k Ω	8	kV

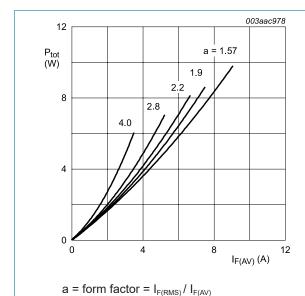


Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

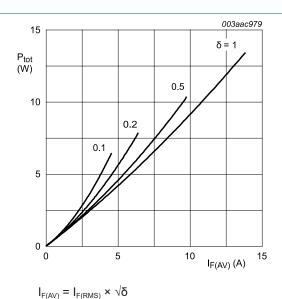


Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	1.6	K/W
	mounting base	with heatsink compound; per diode; <u>Fig 3</u>	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	60	-	K/W

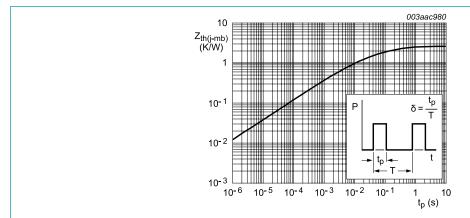
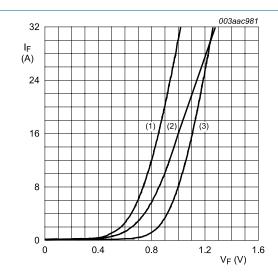


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

0	D	0	NA:	T	B.0	11-24
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.72	0.85	V
		$I_F = 20 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	1	1.15	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C	-	6	30	μA
		$V_R = 200 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.2	0.6	mA
Dynamic	characteristics					
Q_r	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}$	-	8	12.5	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5	-	20	25	ns
		I_F = 0.5 A to I_R = 1 A; T_j = 25 °C; measured at I_R = 0.25 A; step recovery; Fig. 6	-	10	20	ns
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	-	1	V



(1) T_j = 150 °C; typical values

(2) $T_j = 150$ °C; maximum values

(3) $T_j = 25$ °C; maximum values

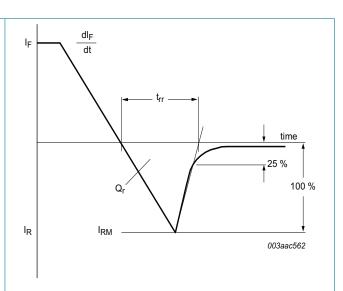


Fig. 5. Reverse recovery definitions; ramp recovery



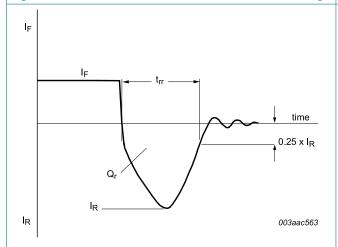


Fig. 6. Reverse recovery definitions; step recovery

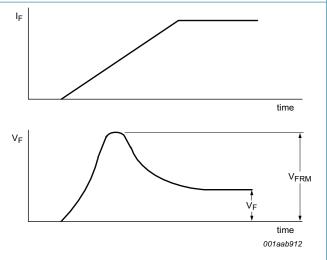
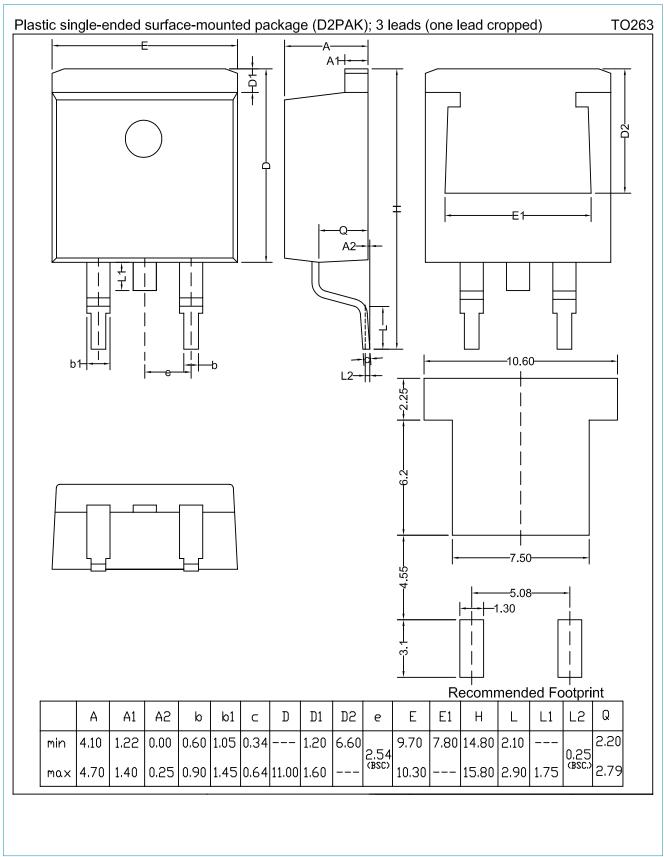


Fig. 7. Forward recovery definitions

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BYV32EB-200

Dual ultrafast power diode

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